# **Complementary Silicon Plastic Power Transistors**

... designed for use in general purpose amplifier and switching applications. Compact TO-220 AB package.

#### **MAXIMUM RATINGS**

Rating	Symbol	TIP29B TIP30B	TIP29C TIP30C	Unit
Collector–Emitter Voltage	VCEO	80	100	Vdc
Collector-Base Voltage	VCB	80	100	Vdc
Emitter–Base Voltage	VEB	5.	Vdc	
Collector Current — Continuous Peak	IC	1. 3.	Adc	
Base Current	ΙB	0.	Adc	
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	3 0.:	Watts W/°C	
Total Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	2. 0.0	Watts W/°C	
Unclamped Inductive Load Energy (See Note 3)	E	3	2-60	mJ
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	−65 to	+150	°C

#### THERMAL CHARACTERISTICS

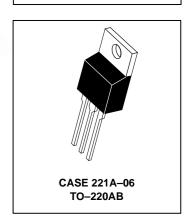
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	R <sub>θ</sub> JA	62.5	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	4.167	°C/W

## TIP29B

### TIP29C PNP TIP30B

TIP30C

1 AMPERE
POWER TRANSISTORS
COMPLEMENTARY
SILICON
80-100 VOLTS
30 WATTS



**ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (1) (I <sub>C</sub> = 30 mAdc, I <sub>B</sub> = 0)	TIP29B, TIP30B TIP29C, TIP30C	VCEO(sus)	80 100	_ _	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 60 Vdc, I <sub>B</sub> = 0)		ICEO	_	0.3	mAdc
Collector Cutoff Current (VCE = 80 Vdc, VEB = 0) (VCE = 100 Vdc, VEB = 0)	TIP29B, TIP30B TIP29C, TIP30C	ICES		200 200	μAdc
Emitter Cutoff Current (VBE = 5.0 Vdc, IC =	0)	I <sub>EBO</sub>	_	1.0	mAdc
ON CHARACTERISTICS (1)					
DC Current Gain ( $I_C = 0.2$ Adc, $V_{CE} = 4.0$ ( $I_C = 1.0$ Adc, $V_{CE} = 4.0$		hFE	40 15	— 75	_
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 1	.0 Adc, I <sub>B</sub> = 125 mAdc)	VCE(sat)	_	0.7	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = 1.0 Adc, V <sub>C</sub>	E = 4.0 Vdc)	V <sub>BE(on)</sub>	_	1.3	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product (2) (I <sub>C</sub> = 200 mAdc, V <sub>CE</sub> = 10 Vdc, f <sub>test</sub> = 1.	0 MHz)	fΤ	3.0	_	MHz
Small-Signal Current Gain (I <sub>C</sub> = 0.2 Adc, V <sub>0</sub>	CE = 10 Vdc, f = 1.0 kHz)	h <sub>fe</sub>	20	_	_

- (1) Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.
- (2)  $f_T = |h_{fe}| \cdot f_{test}$ .
- (3) This rating based on testing with  $L_C = 20$  mH,  $R_{BE} = 100 \Omega$ ,  $V_{CC} = 10$  V,  $I_C = 1.8$  A, P.R.F = 10 Hz.

#### REV 1



#### **TIP29B TIP29C TIP30B TIP30C**

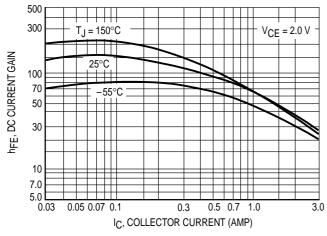


Figure 1. DC Current Gain

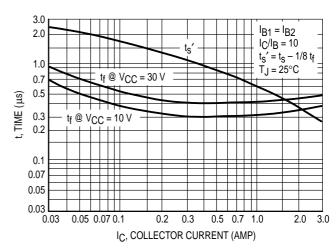


Figure 2. Turn-Off Time

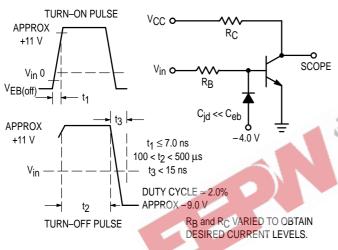


Figure 3. Switching Time Equivalent Circuit

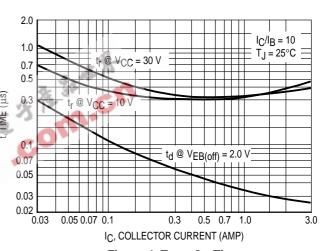


Figure 4. Turn-On Time

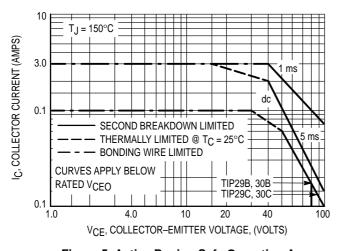


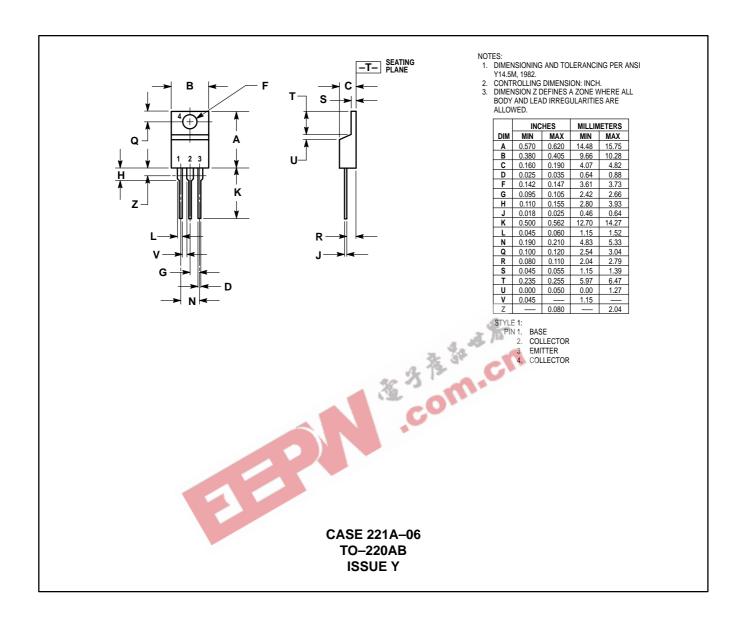
Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_{\text{C}} - V_{\text{CE}}$  operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on  $T_{J(pk)} = 150^{\circ}C$ ;  $T_{C}$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \le 150^{\circ}C$ . At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

#### **TIP29B TIP29C TIP30B TIP30C**

#### **PACKAGE DIMENSIONS**



#### TIP29B TIP29C TIP30B TIP30C



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